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Understanding **Embedded - FPGAs (Field Programmable Gate Array)**

Embedded - FPGAs, or Field Programmable Gate Arrays, are advanced integrated circuits that offer unparalleled flexibility and performance for digital systems. Unlike traditional fixed-function logic devices, FPGAs can be programmed and reprogrammed to execute a wide array of logical operations, enabling customized functionality tailored to specific applications. This reprogrammability allows developers to iterate designs quickly and implement complex functions without the need for custom hardware.

Applications of Embedded - FPGAs

The versatility of Embedded - FPGAs makes them indispensable in numerous fields. In telecommunications.

Details

Product Status	Active
Number of LABs/CLBs	18840
Number of Logic Elements/Cells	241152
Total RAM Bits	15335424
Number of I/O	600
Number of Gates	-
Voltage - Supply	0.95V ~ 1.05V
Mounting Type	Surface Mount
Operating Temperature	-40°C ~ 100°C (TJ)
Package / Case	1156-BBGA, FCBGA
Supplier Device Package	1156-FCBGA (35x35)
Purchase URL	https://www.e-xfl.com/product-detail/xilinx/xc6vlx240t-1ffg1156i

Table 3: DC Characteristics Over Recommended Operating Conditions (1)(2)

Symbol	Description	Min	Typ	Max	Units
V_{DRINT}	Data retention V_{CCINT} voltage (below which configuration data might be lost)	0.75	–	–	V
V_{DRI}	Data retention V_{CCAUX} voltage (below which configuration data might be lost)	2.0	–	–	V
I_{REF}	V_{REF} leakage current per pin	–	–	10	μA
I_L	Input or output leakage current per pin (sample-tested)	–	–	10	μA
$C_{IN}^{(3)}$	Die input capacitance at the pad	–	–	8	pF
I_{RPU}	Pad pull-up (when selected) @ $V_{IN} = 0V$, $V_{CCO} = 2.5V$	20	–	80	μA
	Pad pull-up (when selected) @ $V_{IN} = 0V$, $V_{CCO} = 1.8V$	8	–	40	μA
	Pad pull-up (when selected) @ $V_{IN} = 0V$, $V_{CCO} = 1.5V$	5	–	30	μA
	Pad pull-up (when selected) @ $V_{IN} = 0V$, $V_{CCO} = 1.2V$	1	–	20	μA
I_{RPD}	Pad pull-down (when selected) @ $V_{IN} = 2.5V$	3	–	80	μA
I_{BATT}	Battery supply current	–	–	150	nA
n	Temperature diode ideality factor	–	1.0002	–	n
r	Series resistance	–	5	–	Ω

Notes:

1. Typical values are specified at nominal voltage, 25°C.
2. Maximum value specified for worst case process at 25°C.
3. This measurement represents the die capacitance at the pad, not including the package.

Table 4: Typical Quiescent Supply Current (Cont'd)

Symbol	Description	Device	Speed and Temperature Grade						Units
			-3 (C)	-2 (C, E, & I)	-1 (C & I)	-1 (I & M) ⁽²⁾	-1L (C)	-1L (I) ⁽¹⁾	
I_{CC0Q}	Quiescent V_{CC0} supply current	XC6VLX75T	1	1	1	N/A	1	1	mA
		XC6VLX130T	1	1	1	N/A	1	1	mA
		XC6VLX195T	1	1	1	N/A	1	1	mA
		XC6VLX240T	2	2	2	N/A	2	2	mA
		XC6VLX365T	2	2	2	N/A	2	2	mA
		XC6VLX550T ⁽³⁾	N/A	3	3	N/A	3	3	mA
		XC6VLX760 ⁽³⁾	N/A	3	3	N/A	3	3	mA
		XC6VSX315T	2	2	2	N/A	2	2	mA
		XC6VSX475T ⁽³⁾	N/A	2	2	N/A	2	2	mA
		XC6VHX250T	1	1	1	N/A	N/A	N/A	mA
		XC6VHX255T	1	1	1	N/A	N/A	N/A	mA
		XC6VHX380T ⁽⁴⁾	2	2	2	N/A	N/A	N/A	mA
		XC6VHX565T ⁽⁵⁾	N/A	2	2	N/A	N/A	N/A	mA
		XQ6VLX130T	N/A	1	N/A	1	N/A	1	mA
		XQ6VLX240T	N/A	2	N/A	2	N/A	2	mA
		XQ6VLX550T ⁽⁷⁾	N/A	N/A	N/A	3	N/A	3	mA
		XQ6VSX315T	N/A	2	N/A	2	N/A	2	mA
		XQ6VSX475T ⁽⁷⁾	N/A	N/A	N/A	2	N/A	2	mA

Table 6: Power Supply Ramp Time

Symbol	Description	Ramp Time	Units
V _{CCINT}	Internal supply voltage relative to GND	0.20 to 50.0	ms
V _{CCO}	Output drivers supply voltage relative to GND	0.20 to 50.0	ms
V _{CCAUX}	Auxiliary supply voltage relative to GND	0.20 to 50.0	ms

SelectIO™ DC Input and Output Levels

Values for V_{IL} and V_{IH} are recommended input voltages. Values for I_{OL} and I_{OH} are guaranteed over the recommended operating conditions at the V_{OL} and V_{OH} test points. Only selected standards are tested. These are chosen to ensure that all standards meet their specifications. The selected standards are tested at a minimum V_{CCO} with the respective V_{OL} and V_{OH} voltage levels shown. Other standards are sample tested.

Table 7: SelectIO DC Input and Output Levels

I/O Standard	V _{IL}		V _{IH}		V _{OL}	V _{OH}	I _{OL}	I _{OH}
	V, Min	V, Max	V, Min	V, Max	V, Max	V, Min	mA	mA
LVCMOS25, LVDCI25	-0.3	0.7	1.7	V _{CCO} + 0.3	0.4	V _{CCO} - 0.4	Note(3)	Note(3)
LVCMOS18, LVDCI18	-0.3	35% V _{CCO}	65% V _{CCO}	V _{CCO} + 0.3	0.45	V _{CCO} - 0.45	Note(4)	Note(4)
LVCMOS15, LVDCI15	-0.3	35% V _{CCO}	65% V _{CCO}	V _{CCO} + 0.3	25% V _{CCO}	75% V _{CCO}	Note(4)	Note(4)
LVCMOS12	-0.3	35% V _{CCO}	65% V _{CCO}	V _{CCO} + 0.3	25% V _{CCO}	75% V _{CCO}	Note(5)	Note(5)
HSTL I_12	-0.3	V _{REF} - 0.1	V _{REF} + 0.1	V _{CCO} + 0.3	25% V _{CCO}	75% V _{CCO}	6.3	6.3
HSTL I ⁽²⁾	-0.3	V _{REF} - 0.1	V _{REF} + 0.1	V _{CCO} + 0.3	0.4	V _{CCO} - 0.4	8	-8
HSTL II ⁽²⁾	-0.3	V _{REF} - 0.1	V _{REF} + 0.1	V _{CCO} + 0.3	0.4	V _{CCO} - 0.4	16	-16
HSTL III ⁽²⁾	-0.3	V _{REF} - 0.1	V _{REF} + 0.1	V _{CCO} + 0.3	0.4	V _{CCO} - 0.4	24	-8
DIFF HSTL I ⁽²⁾	-0.3	50% V _{CCO} - 0.1	50% V _{CCO} + 0.1	V _{CCO} + 0.3	-	-	-	-
DIFF HSTL II ⁽²⁾	-0.3	50% V _{CCO} - 0.1	50% V _{CCO} + 0.1	V _{CCO} + 0.3	-	-	-	-
SSTL2 I	-0.3	V _{REF} - 0.15	V _{REF} + 0.15	V _{CCO} + 0.3	V _{TT} - 0.61	V _{TT} + 0.61	8.1	-8.1
SSTL2 II	-0.3	V _{REF} - 0.15	V _{REF} + 0.15	V _{CCO} + 0.3	V _{TT} - 0.81	V _{TT} + 0.81	16.2	-16.2
DIFF SSTL2 I	-0.3	50% V _{CCO} - 0.15	50% V _{CCO} + 0.15	V _{CCO} + 0.3	-	-	-	-
DIFF SSTL2 II	-0.3	50% V _{CCO} - 0.15	50% V _{CCO} + 0.15	V _{CCO} + 0.3	-	-	-	-
SSTL18 I	-0.3	V _{REF} - 0.125	V _{REF} + 0.125	V _{CCO} + 0.3	V _{TT} - 0.47	V _{TT} + 0.47	6.7	-6.7
SSTL18 II	-0.3	V _{REF} - 0.125	V _{REF} + 0.125	V _{CCO} + 0.3	V _{TT} - 0.60	V _{TT} + 0.60	13.4	-13.4
DIFF SSTL18 I	-0.3	50% V _{CCO} - 0.125	50% V _{CCO} + 0.125	V _{CCO} + 0.3	-	-	-	-
DIFF SSTL18 II	-0.3	50% V _{CCO} - 0.125	50% V _{CCO} + 0.125	V _{CCO} + 0.3	-	-	-	-
SSTL15	-0.3	V _{REF} - 0.1	V _{REF} + 0.1	V _{CCO} + 0.3	V _{TT} - 0.175	V _{TT} + 0.175	14.3	14.3

Notes:

1. Tested according to relevant specifications.
2. Applies to both 1.5V and 1.8V HSTL.
3. Using drive strengths of 2, 4, 6, 8, 12, 16, or 24 mA.
4. Using drive strengths of 2, 4, 6, 8, 12, or 16 mA.
5. Supported drive strengths of 2, 4, 6, or 8 mA.
6. For detailed interface specific DC voltage levels, see [UG361: Virtex-6 FPGA SelectIO Resources User Guide](#).

HT DC Specifications (HT_25)

Table 8: HT DC Specifications

Symbol	DC Parameter	Conditions	Min	Typ	Max	Units
V_{CCO}	Supply Voltage		2.38	2.5	2.63	V
V_{OD}	Differential Output Voltage for XC devices	$R_T = 100 \Omega$ across Q and \bar{Q} signals	480	600	885	mV
	Differential Output Voltage for XQ devices		480	600	930	mV
ΔV_{OD}	Change in V_{OD} Magnitude		-15	-	15	mV
V_{OCM}	Output Common Mode Voltage	$R_T = 100 \Omega$ across Q and \bar{Q} signals	440	600	760	mV
ΔV_{OCM}	Change in V_{OCM} Magnitude		-15	-	15	mV
V_{ID}	Input Differential Voltage		200	600	1000	mV
ΔV_{ID}	Change in V_{ID} Magnitude		-15	-	15	mV
V_{ICM}	Input Common Mode Voltage		440	600	780	mV
ΔV_{ICM}	Change in V_{ICM} Magnitude		-15	-	15	mV

LVDS DC Specifications (LVDS_25)

Table 9: LVDS DC Specifications

Symbol	DC Parameter	Conditions	Min	Typ	Max	Units
V_{CCO}	Supply Voltage		2.38	2.5	2.63	V
V_{OH}	Output High Voltage for Q and \bar{Q}	$R_T = 100 \Omega$ across Q and \bar{Q} signals	-	-	1.675	V
V_{OL}	Output Low Voltage for Q and \bar{Q}	$R_T = 100 \Omega$ across Q and \bar{Q} signals	0.825	-	-	V
V_{ODIFF}	Differential Output Voltage ($Q - \bar{Q}$), Q = High ($\bar{Q} - Q$), \bar{Q} = High	$R_T = 100 \Omega$ across Q and \bar{Q} signals	247	350	600	mV
V_{OCM}	Output Common-Mode Voltage for XC devices	$R_T = 100 \Omega$ across Q and \bar{Q} signals	1.075	1.250	1.425	V
	Output Common-Mode Voltage for XQ devices		1.000	1.250	1.425	V
V_{IDIFF}	Differential Input Voltage ($Q - \bar{Q}$), Q = High ($\bar{Q} - Q$), \bar{Q} = High		100	350	600	mV
V_{ICM}	Input Common-Mode Voltage		0.3	1.2	2.2	V

Extended LVDS DC Specifications (LVDSEXT_25)

Table 10: Extended LVDS DC Specifications

Symbol	DC Parameter	Conditions	Min	Typ	Max	Units
V_{CCO}	Supply Voltage		2.38	2.5	2.63	V
V_{OH}	Output High Voltage for Q and \bar{Q}	$R_T = 100 \Omega$ across Q and \bar{Q} signals	-	-	1.785	V
V_{OL}	Output Low Voltage for Q and \bar{Q}	$R_T = 100 \Omega$ across Q and \bar{Q} signals	0.715	-	-	V
V_{ODIFF}	Differential Output Voltage ($Q - \bar{Q}$), Q = High ($\bar{Q} - Q$), \bar{Q} = High for XC devices	$R_T = 100 \Omega$ across Q and \bar{Q} signals	350	-	840	mV
	Differential Output Voltage ($Q - \bar{Q}$), Q = High ($\bar{Q} - Q$), \bar{Q} = High for XQ devices		350	-	850	mV
V_{OCM}	Output Common-Mode Voltage for XC devices	$R_T = 100 \Omega$ across Q and \bar{Q} signals	1.075	1.250	1.425	V
	Output Common-Mode Voltage for XQ devices		1.000	1.250	1.425	V
V_{IDIFF}	Differential Input Voltage ($Q - \bar{Q}$), Q = High ($\bar{Q} - Q$), \bar{Q} = High	Common-mode input voltage = 1.25V	100	-	1000	mV
V_{ICM}	Input Common-Mode Voltage	Differential input voltage = ± 350 mV	0.3	1.2	2.2	V

Table 16: GTX Transceiver Quiescent Supply Current (per Lane) ⁽¹⁾⁽²⁾⁽³⁾

Symbol	Description	Typ ⁽⁴⁾	Max	Units
IMGTAVTTQ	Quiescent MGTAVTT supply current for one GTX transceiver	0.9	Note 2	mA
IMGTAVCCQ	Quiescent MGTAVCC supply current for one GTX transceiver	3.5		mA

Notes:

1. Device powered and unconfigured.
2. Currents for conditions other than values specified in this table can be obtained by using the XPE or XPA tools.
3. GTX transceiver quiescent supply current for an entire device can be calculated by multiplying the values in this table by the number of available GTX transceivers.
4. Typical values are specified at nominal voltage, 25°C.

GTX Transceiver DC Input and Output Levels

Table 17 summarizes the DC output specifications of the GTX transceivers in Virtex-6 FPGAs. Consult [UG366: Virtex-6 FPGA GTX Transceivers User Guide](#) for further details.

Table 17: GTX Transceiver DC Specifications

Symbol	DC Parameter	Conditions	Min	Typ	Max	Units
DV _{PPIN}	Differential peak-to-peak input voltage	External AC coupled ≤ 4.25 Gb/s	125	–	2000	mV
		External AC coupled > 4.25 Gb/s	175	–	2000	mV
V _{IN}	Absolute input voltage	DC coupled MGTAVTT = 1.2V	–400	–	MGTAVTT	mV
V _{CMIN}	Common mode input voltage	DC coupled MGTAVTT = 1.2V	–	2/3 MGTAVTT	–	mV
DV _{PPOUT}	Differential peak-to-peak output voltage ⁽¹⁾	Transmitter output swing is set to maximum setting	–	–	1000	mV
V _{CMOUTDC}	DC common mode output voltage.	Equation based	MGTAVTT – DV _{PPOUT} /4			mV
R _{IN}	Differential input resistance		80	100	130	Ω
R _{OUT}	Differential output resistance		80	100	120	Ω
T _{OSKEW}	Transmitter output pair (TXP and TXN) intra-pair skew		–	2	8	ps
C _{EXT}	Recommended external AC coupling capacitor ⁽²⁾		–	100	–	nF

Notes:

1. The output swing and preemphasis levels are programmable using the attributes discussed in [UG366: Virtex-6 FPGA GTX Transceivers User Guide](#) and can result in values lower than reported in this table.
2. Other values can be used as appropriate to conform to specific protocols and standards.

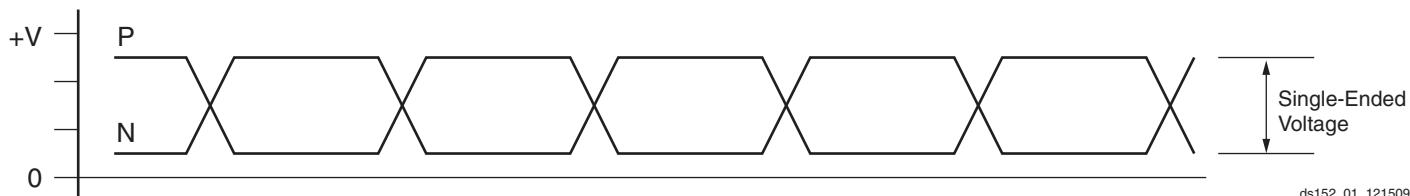


Figure 1: Single-Ended Peak-to-Peak Voltage

Table 21: GTX Transceiver Reference Clock Switching Characteristics

Symbol	Description	Conditions	All Speed Grades			Units
			Min	Typ	Max	
F_{GCLK}	Reference clock frequency range		62.5	—	650	MHz
T_{RCLK}	Reference clock rise time	20% – 80%	—	200	—	ps
T_{FCLK}	Reference clock fall time	80% – 20%	—	200	—	ps
T_{DCREF}	Reference clock duty cycle	Transceiver PLL only	45	50	55	%
T_{LOCK}	Clock recovery frequency acquisition time	Initial PLL lock	—	—	1	ms
T_{PHASE}	Clock recovery phase acquisition time	Lock to data after PLL has locked to the reference clock	—	—	200	μs

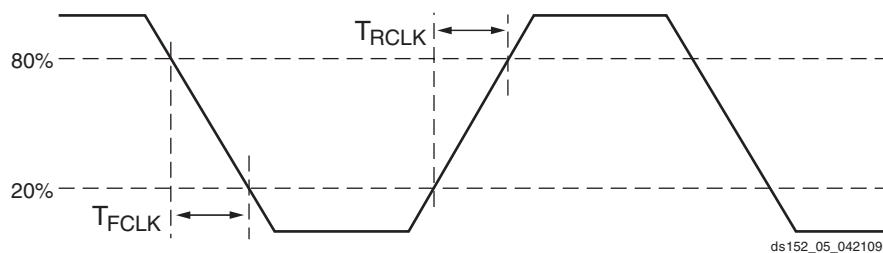


Figure 3: Reference Clock Timing Parameters

Table 22: GTX Transceiver User Clock Switching Characteristics⁽¹⁾

Symbol	Description	Conditions	Speed Grade				Units
			-3	-2	-1	-1L	
F_{TXOUT}	TXOUTCLK maximum frequency	Internal 20-bit data path	330	330	250	250	MHz
		Internal 16-bit data path	412.5	412.5	312.5	250	MHz
F_{RXREC}	RXRECCLK maximum frequency	Internal 20-bit data path	330	330	250	250	MHz
		Internal 16-bit data path	412.5	412.5	312.5	250	MHz
T_{RX}	RXUSRCLK maximum frequency		412.5 ⁽²⁾	412.5 ⁽²⁾	312.5	250	MHz
T_{RX2}	RXUSRCLK2 maximum frequency	1 byte interface	376	376	312.5	250	MHz
		2 byte interface	406.25	406.25	312.5	250	MHz
		4 byte interface	206.25	206.25	156.25	125	MHz
T_{TX}	TXUSRCLK maximum frequency		412.5 ⁽³⁾	412.5 ⁽³⁾	312.5	250	MHz
T_{TX2}	TXUSRCLK2 maximum frequency	1 byte interface	376	376	312.5	250	MHz
		2 byte interface	406.25	406.25	312.5	250	MHz
		4 byte interface	206.25	206.25	156.25	125	MHz

Notes:

1. Clocking must be implemented as described in [UG366: Virtex-6 FPGA GTX Transceivers User Guide](#).
2. 406.25 MHz when the RX elastic buffer is bypassed.
3. 406.25 MHz when the TX buffer is bypassed.

Table 23: GTX Transceiver Transmitter Switching Characteristics

Symbol	Description	Condition	Min	Typ	Max	Units
F_{GTXTX}	Serial data rate range		0.480	—	F_{GTXMAX}	Gb/s
T_{RTX}	TX Rise time	20%–80%	—	120	—	ps
T_{FTX}	TX Fall time	80%–20%	—	120	—	ps
T_{LLSKEW}	TX lane-to-lane skew ⁽¹⁾		—	—	350	ps
$V_{TXOOBVDPDPP}$	Electrical idle amplitude		—	—	15	mV
$T_{TXOOBTTRANSITION}$	Electrical idle transition time		—	—	75	ns
$TJ_{6.5}$	Total Jitter ⁽²⁾⁽³⁾	6.5 Gb/s	—	—	0.33	UI
$DJ_{6.5}$	Deterministic Jitter ⁽²⁾⁽³⁾		—	—	0.17	UI
$TJ_{5.0}$	Total Jitter ⁽²⁾⁽³⁾	5.0 Gb/s	—	—	0.33	UI
$DJ_{5.0}$	Deterministic Jitter ⁽²⁾⁽³⁾		—	—	0.15	UI
$TJ_{4.25}$	Total Jitter ⁽²⁾⁽³⁾	4.25 Gb/s	—	—	0.33	UI
$DJ_{4.25}$	Deterministic Jitter ⁽²⁾⁽³⁾		—	—	0.14	UI
$TJ_{3.75}$	Total Jitter ⁽²⁾⁽³⁾	3.75 Gb/s	—	—	0.34	UI
$DJ_{3.75}$	Deterministic Jitter ⁽²⁾⁽³⁾		—	—	0.16	UI
$TJ_{3.125}$	Total Jitter ⁽²⁾⁽³⁾	3.125 Gb/s	—	—	0.2	UI
$DJ_{3.125}$	Deterministic Jitter ⁽²⁾⁽³⁾		—	—	0.1	UI
$TJ_{3.125L}$	Total Jitter ⁽²⁾⁽³⁾	3.125 Gb/s ⁽⁴⁾	—	—	0.35	UI
$DJ_{3.125L}$	Deterministic Jitter ⁽²⁾⁽³⁾		—	—	0.16	UI
$TJ_{2.5}$	Total Jitter ⁽²⁾⁽³⁾	2.5 Gb/s ⁽⁵⁾	—	—	0.20	UI
$DJ_{2.5}$	Deterministic Jitter ⁽²⁾⁽³⁾		—	—	0.08	UI
$TJ_{1.25}$	Total Jitter ⁽²⁾⁽³⁾	1.25 Gb/s ⁽⁶⁾	—	—	0.15	UI
$DJ_{1.25}$	Deterministic Jitter ⁽²⁾⁽³⁾		—	—	0.06	UI
TJ_{600}	Total Jitter ⁽²⁾⁽³⁾	600 Mb/s	—	—	0.1	UI
DJ_{600}	Deterministic Jitter ⁽²⁾⁽³⁾		—	—	0.03	UI
TJ_{480}	Total Jitter ⁽²⁾⁽³⁾	480 Mb/s	—	—	0.1	UI
DJ_{480}	Deterministic Jitter ⁽²⁾⁽³⁾		—	—	0.03	UI

Notes:

1. Using same REFCLK input with TXENPMAPHASEALIGN enabled for up to 12 consecutive transmitters (three fully populated GTX Quads).
2. Using PLL_DIVSEL_FB = 2, 20-bit internal data width. These values are NOT intended for protocol specific compliance determinations.
3. All jitter values are based on a bit-error ratio of 10^{-12} .
4. PLL frequency at 1.5625 GHz and OUTDIV = 1.
5. PLL frequency at 2.5 GHz and OUTDIV = 2.
6. PLL frequency at 2.5 GHz and OUTDIV = 4.

GTH Transceiver Specifications

GTH Transceiver DC Characteristics

Table 25: Absolute Maximum Ratings for GTH Transceivers⁽¹⁾

Symbol	Description	Min	Max	Units
MGTHAVCC	Analog supply voltage for the GTH transmitter, receiver, and common analog circuits	-0.5	1.125	V
MGTHAVCCRX	Analog supply voltage for the GTH receiver circuits and common analog circuits	-0.5	1.125	V
MGTHAVTT	Analog supply voltage for the GTH transmitter termination circuits	-0.5	1.32	V
MGTHAVCCPLL	Analog supply voltage for the GTH receiver and PLL circuits	-0.5	1.935	V
V _{IN}	Receiver (RXP/RXN) and Transmitter (TXP/TXN) absolute input voltage	-0.5	1.125	V
V _{MGTREFCLK}	Reference clock absolute input voltage	-0.5	1.935	V

Notes:

- Stresses beyond those listed under Absolute Maximum Ratings might cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those listed under Operating Conditions is not implied. Exposure to Absolute Maximum Ratings conditions for extended periods of time might affect device reliability.

Table 26: Recommended Operating Conditions for GTH Transceivers⁽¹⁾⁽²⁾

Symbol	Description	Min	Typ	Max	Units
MGTHAVCC	Analog supply voltage for the GTH transmitter, receiver, and common analog circuits	1.075	1.1	1.125	V
MGTHAVCCRX	Analog supply voltage for the GTH receiver circuits and common analog circuits	1.075	1.1	1.125	V
MGTHAVTT	Analog supply voltage for the GTH transmitter termination circuits	1.140	1.2	1.26	V
MGTHAVCCPLL	Analog supply voltage for the GTH receiver and PLL circuit	1.710	1.8	1.89	V

Notes:

- Each voltage listed requires the filter circuit described in [UG371: Virtex-6 FPGA GTH Transceivers User Guide](#).
- Voltages are specified for the temperature range of $T_j = -40^{\circ}\text{C}$ to $+100^{\circ}\text{C}$.

Table 27: GTH Transceiver Power Supply Sequencing⁽¹⁾⁽²⁾⁽³⁾

Symbol	Description	Min	Max	Units
T _{HAVCC2HAVCCRX}	Maximum time between powering MGTHAVCC to when MGTHAVCCRX must be powered.	0	5	ms
T _{HAVCCRX2HAVCCPLL}	Minimum time between powering MGTHAVCCRX to when MGTHAVCCPLL can be powered.	10	–	μs
T _{HAVCCRX2HAVTT}	Minimum time between powering MGTHAVCCRX to when MGTHAVTT can be powered.	10	–	μs

Notes:

- MGTHAVCCRX must be powered simultaneously or within T_{HAVCC2HAVCCRX} of MGTHAVCC, but it must not precede MGTHAVCC.
- MGTHAVCC and MGTHAVCCRX must be powered before MGTHAVCCPLL and MGTHAVTT. This minimum time is defined by T_{HAVCCRX2HAVCCPLL} and T_{HAVCCRX2HAVTT}.
- At any time, the condition of MGTHAVCC being present and MGTHAVCCRX not being present should not occur for more than the maximum T_{HAVCC2HAVCCRX}.

GTH Transceiver DC Input and Output Levels

Table 30 summarizes the DC output specifications of the GTH transceivers in Virtex-6 FPGAs. Consult [UG371: Virtex-6 FPGA GTH Transceivers User Guide](#) for further details.

Table 30: GTH Transceiver DC Specifications

Symbol	DC Parameter	Conditions	Min	Typ	Max	Units
D _{VPPIN}	Differential peak-to-peak input voltage	External AC coupled	175	—	1200	mV
D _{VPPOUT}	Differential peak-to-peak output voltage ⁽¹⁾	Transmitter output swing is set to maximum setting	800	—	1200	mV
R _{IN}	Differential input resistance		80	100	120	Ω
R _{OUT}	Differential output resistance		80	100	120	Ω
T _{OSKew}	Transmitter output pair (TXP and TXN) intra-pair skew		—	2	—	ps
C _{EXT}	Recommended external AC coupling capacitor ⁽²⁾		—	100	—	nF

Notes:

1. The output swing and preemphasis levels are programmable using the attributes discussed in [UG371: Virtex-6 FPGA GTH Transceivers User Guide](#) and can result in values lower than reported in this table.
2. Other values can be used as appropriate to conform to specific protocols and standards.

Table 31 summarizes the DC specifications of the clock input of the GTH transceiver. Consult [UG371: Virtex-6 FPGA GTH Transceivers User Guide](#) for further details.

Table 31: GTH Transceiver Clock DC Input Level Specification

Symbol	DC Parameter	Conditions	Min	Typ	Max	Units
V _{IDIFF}	Differential peak-to-peak input voltage	≤ 600 MHz	500	—	1600	mV
		> 600 MHz	600	—	1600	mV
R _{IN}	Differential input resistance		80	100	120	Ω
C _{EXT}	Required external AC coupling capacitor		—	100	—	nF

GTH Transceiver Switching Characteristics

Consult [UG371: Virtex-6 FPGA GTH Transceivers User Guide](#) for further information.

Table 32: GTH Transceiver Maximum Data Rate and PLL Frequency Range

Symbol	Description	Conditions	Speed Grade			Units
			-3	-2	-1	
F_{GTHMAX}	Maximum GTH transceiver data rate	PLL Output Divider = 1	11.182	11.182	10.32	Gb/s
		PLL Output Divider = 4	2.795	2.795	2.58	Gb/s
F_{GTHMIN}	Minimum GTH transceiver data rate ⁽¹⁾	PLL Output Divider = 1	9.92	9.92	9.92	Gb/s
		PLL Output Divider = 4	2.48	2.48	2.48	Gb/s
$F_{GPLLMAX}$	Maximum GTH PLL frequency		5.591	5.591	5.16	GHz
$F_{GPLLMIN}$	Minimum GTH PLL frequency		4.96	4.96	4.96	GHz

Notes:

- Lower data rates can be achieved using FPGA logic based oversampling designs.

Table 33: GTH Transceiver Dynamic Reconfiguration Port (DRP) Switching Characteristics

Symbol	Description	Speed Grade			Units
		-3	-2	-1	
$F_{GTHDRPCLK}$	GTHDRPCLK maximum frequency	70	70	60	MHz

Table 34: GTH Transceiver Reference Clock Switching Characteristics

Symbol	Description	Conditions	All Speed Grades			Units
			Min	Typ	Max	
F_{GCLK}	Reference clock frequency range	-1 speed grade	150	–	645	MHz
		-2 and -3 speed grades	150	–	700	MHz
T_{RCLK}	Reference clock rise time	20% – 80%	–	200	–	ps
T_{FCLK}	Reference clock fall time	80% – 20%	–	200	–	ps
T_{DCREF}	Reference clock duty cycle	CLK	45	50	55	%
T_{LOCK}	Clock recovery frequency acquisition time	Initial PLL lock	–	–	2	ms
T_{PHASE}	Clock recovery phase acquisition time	Lock to data after PLL has locked to the reference clock	–	–	20	μs

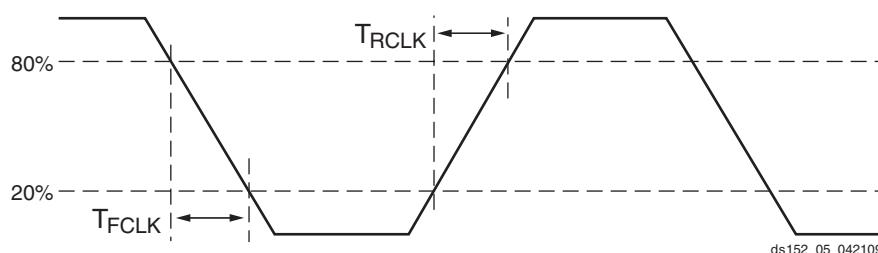


Figure 5: Reference Clock Timing Parameters

Switching Characteristics

All values represented in this data sheet are based on these speed specifications: v1.17 for -3, -2, and -1; and v1.10 for -1L. Switching characteristics are specified on a per-speed-grade basis and can be designated as Advance, Preliminary, or Production. Each designation is defined as follows:

Advance

These specifications are based on simulations only and are typically available soon after device design specifications are frozen. Although speed grades with this designation are considered relatively stable and conservative, some under-reporting might still occur.

Preliminary

These specifications are based on complete ES (engineering sample) silicon characterization. Devices and speed grades with this designation are intended to give a better indication of the expected performance of production silicon. The probability of under-reporting delays is greatly reduced as compared to Advance data.

Production

These specifications are released once enough production silicon of a particular device family member has been characterized to provide full correlation between specifications and devices over numerous production lots. There is no under-reporting of delays, and customers receive formal notification of any subsequent changes. Typically, the slowest speed grades transition to Production before faster speed grades.

All specifications are always representative of worst-case supply voltage and junction temperature conditions.

Since individual family members are produced at different times, the migration from one category to another depends completely on the status of the fabrication process for each device.

[Table 42](#) correlates the current status of each Virtex-6 device on a per speed grade basis.

Table 42: Virtex-6 Device Speed Grade Designations

Device	Speed Grade Designations		
	Advance	Preliminary	Production
XC6VLX75T			-3, -2, -1, -1L
XC6VLX130T			-3, -2, -1, -1L
XC6VLX195T			-3, -2, -1, -1L
XC6VLX240T			-3, -2, -1, -1L
XC6VLX365T			-3, -2, -1, -1L
XC6VLX550T			-2, -1, -1L
XC6VLX760			-2, -1, -1L
XC6VSX315T			-3, -2, -1, -1L
XC6VSX475T			-2, -1, -1L
XC6VHX250T			-3, -2, -1
XC6VHX255T			-3, -2, -1
XC6VHX380T			-3, -2, -1
XC6VHX565T			-2, -1
XQ6VLX130T			-2, -1, -1L
XQ6VLX240T			-2, -1, -1L
XQ6VLX550T			-1, -1L
XQ6VSX315T			-2, -1, -1L
XQ6VSX475T			-1, -1L

Testing of Switching Characteristics

All devices are 100% functionally tested. Internal timing parameters are derived from measuring internal test patterns. Listed below are representative values.

For more specific, more precise, and worst-case guaranteed data, use the values reported by the static timing analyzer and back-annotate to the simulation net list. Unless otherwise noted, values apply to all Virtex-6 devices.

IOB Pad Input/Output/3-State Switching Characteristics

Table 44 (for commercial (XC) Virtex-6 devices) and **Table 45** (for the Defense-grade (XQ) Virtex-6 devices) summarizes the values of standard-specific data input delay adjustments, output delays terminating at pads (based on standard) and 3-state delays.

T_{IOP} is described as the delay from IOB pad through the input buffer to the I-pin of an IOB pad. The delay varies depending on the capability of the SelectIO input buffer.

T_{IOP} is described as the delay from the O pin to the IOB pad through the output buffer of an IOB pad. The delay varies depending on the capability of the SelectIO output buffer.

T_{IOTP} is described as the delay from the T pin to the IOB pad through the output buffer of an IOB pad, when 3-state is disabled. The delay varies depending on the SelectIO capability of the output buffer.

Table 46 summarizes the value of T_{IOTPHZ} . T_{IOTPHZ} is described as the delay from the T pin to the IOB pad through the output buffer of an IOB pad, when 3-state is enabled (i.e., a high impedance state).

Table 44: IOB Switching Characteristics for the Commercial (XC) Virtex-6 Devices

I/O Standard	T_{IOP}				T_{IOP}				T_{IOTP}				Units	
	Speed Grade				Speed Grade				Speed Grade					
	-3	-2	-1	-1L	-3	-2	-1	-1L	-3	-2	-1	-1L		
LVDS_25	0.85	0.94	1.09	1.08	1.45	1.54	1.68	1.62	1.45	1.54	1.68	1.62	ns	
LVDSEXT_25	0.85	0.94	1.09	1.08	1.53	1.65	1.84	1.73	1.53	1.65	1.84	1.73	ns	
HT_25	0.85	0.94	1.09	1.08	1.51	1.62	1.78	1.69	1.51	1.62	1.78	1.69	ns	
BLVDS_25	0.85	0.94	1.09	1.08	1.39	1.50	1.67	1.65	1.39	1.50	1.67	1.65	ns	
RSDS_25 (point to point)	0.85	0.94	1.09	1.08	1.45	1.54	1.68	1.62	1.45	1.54	1.68	1.62	ns	
HSTL_I	0.81	0.91	1.06	1.06	1.45	1.56	1.73	1.71	1.45	1.56	1.73	1.71	ns	
HSTL_II	0.81	0.91	1.06	1.06	1.44	1.56	1.74	1.72	1.44	1.56	1.74	1.72	ns	
HSTL_III	0.81	0.91	1.06	1.06	1.42	1.54	1.71	1.69	1.42	1.54	1.71	1.69	ns	
HSTL_I_18	0.81	0.91	1.06	1.06	1.47	1.58	1.75	1.72	1.47	1.58	1.75	1.72	ns	
HSTL_II_18	0.81	0.91	1.06	1.06	1.50	1.62	1.81	1.78	1.50	1.62	1.81	1.78	ns	
HSTL_III_18	0.81	0.91	1.06	1.06	1.42	1.54	1.71	1.69	1.42	1.54	1.71	1.69	ns	
SSTL2_I	0.81	0.91	1.06	1.06	1.49	1.60	1.77	1.74	1.49	1.60	1.77	1.74	ns	
SSTL2_II	0.81	0.91	1.06	1.06	1.42	1.54	1.72	1.71	1.42	1.54	1.72	1.71	ns	
SSTL15	0.81	0.91	1.06	1.06	1.42	1.54	1.71	1.69	1.42	1.54	1.71	1.69	ns	
LVCMOS25, Slow, 2 mA	0.51	0.57	0.66	0.70	5.09	5.46	6.01	5.63	5.09	5.46	6.01	5.63	ns	
LVCMOS25, Slow, 4 mA	0.51	0.57	0.66	0.70	3.30	3.49	3.79	3.65	3.30	3.49	3.79	3.65	ns	
LVCMOS25, Slow, 6 mA	0.51	0.57	0.66	0.70	2.62	2.81	3.08	2.95	2.62	2.81	3.08	2.95	ns	
LVCMOS25, Slow, 8 mA	0.51	0.57	0.66	0.70	2.21	2.41	2.72	2.59	2.21	2.41	2.72	2.59	ns	
LVCMOS25, Slow, 12 mA	0.51	0.57	0.66	0.70	1.80	1.95	2.17	2.10	1.80	1.95	2.17	2.10	ns	
LVCMOS25, Slow, 16 mA	0.51	0.57	0.66	0.70	1.89	2.05	2.29	2.21	1.89	2.05	2.29	2.21	ns	
LVCMOS25, Slow, 24 mA	0.51	0.57	0.66	0.70	1.68	1.82	2.02	1.98	1.68	1.82	2.02	1.98	ns	
LVCMOS25, Fast, 2 mA	0.51	0.57	0.66	0.70	5.12	5.49	6.04	5.62	5.12	5.49	6.04	5.62	ns	
LVCMOS25, Fast, 4 mA	0.51	0.57	0.66	0.70	3.28	3.50	3.82	3.65	3.28	3.50	3.82	3.65	ns	
LVCMOS25, Fast, 6 mA	0.51	0.57	0.66	0.70	2.56	2.73	2.99	2.88	2.56	2.73	2.99	2.88	ns	
LVCMOS25, Fast, 8 mA	0.51	0.57	0.66	0.70	2.11	2.33	2.65	2.53	2.11	2.33	2.65	2.53	ns	
LVCMOS25, Fast, 12 mA	0.51	0.57	0.66	0.70	1.74	1.88	2.08	2.03	1.74	1.88	2.08	2.03	ns	
LVCMOS25, Fast, 16 mA	0.51	0.57	0.66	0.70	1.77	1.92	2.13	2.08	1.77	1.92	2.13	2.08	ns	

Table 44: IOB Switching Characteristics for the Commercial (XC) Virtex-6 Devices (Cont'd)

I/O Standard	T _{IOPI}				T _{IOOP}				T _{IOTP}				Units	
	Speed Grade				Speed Grade				Speed Grade					
	-3	-2	-1	-1L	-3	-2	-1	-1L	-3	-2	-1	-1L		
DIFF_SSTL18_I	0.85	0.94	1.09	1.08	1.47	1.58	1.75	1.73	1.47	1.58	1.75	1.73	ns	
DIFF_SSTL18_I_DCI	0.85	0.94	1.09	1.08	1.40	1.51	1.67	1.65	1.40	1.51	1.67	1.65	ns	
DIFF_SSTL18_II	0.85	0.94	1.09	1.08	1.39	1.50	1.67	1.66	1.39	1.50	1.67	1.66	ns	
DIFF_SSTL18_II_DCI	0.85	0.94	1.09	1.08	1.36	1.47	1.63	1.62	1.36	1.47	1.63	1.62	ns	
DIFF_SSTL18_II_T_DCI	0.85	0.94	1.09	1.08	1.40	1.51	1.67	1.65	1.40	1.51	1.67	1.65	ns	
DIFF_SSTL15	0.81	0.91	1.06	1.06	1.42	1.54	1.71	1.69	1.42	1.54	1.71	1.69	ns	
DIFF_SSTL15_DCI	0.81	0.91	1.06	1.06	1.41	1.52	1.68	1.66	1.41	1.52	1.68	1.66	ns	
DIFF_SSTL15_T_DCI	0.81	0.91	1.06	1.06	1.41	1.52	1.68	1.66	1.41	1.52	1.68	1.66	ns	

Table 45: IOB Switching Characteristics for the Defense-grade (XQ) Virtex-6 Devices

I/O Standard	T _{IOPI}			T _{IOOP}			T _{IOTP}			Units	
	Speed Grade			Speed Grade			Speed Grade				
	-2	-1	-1L	-2	-1	-1L	-2	-1	-1L		
LVDS_25	0.94	1.09	1.08	1.54	2.16	1.62	1.54	2.16	1.62	ns	
LVDSEXT_25	0.94	1.09	1.08	1.65	2.20	1.73	1.65	2.20	1.73	ns	
HT_25	0.94	1.09	1.08	1.62	2.20	1.69	1.62	2.20	1.69	ns	
BLVDS_25	0.94	1.09	1.08	1.50	3.18	1.65	1.50	3.18	1.65	ns	
RSDS_25 (point to point)	0.94	1.09	1.08	1.54	2.22	1.62	1.54	2.22	1.62	ns	
HSTL_I	0.91	1.06	1.06	1.56	2.44	1.71	1.56	2.44	1.71	ns	
HSTL_II	0.91	1.06	1.06	1.56	2.21	1.72	1.56	2.21	1.72	ns	
HSTL_III	0.91	1.06	1.06	1.54	2.50	1.69	1.54	2.50	1.69	ns	
HSTL_I_18	0.91	1.06	1.06	1.58	2.43	1.72	1.58	2.43	1.72	ns	
HSTL_II_18	0.91	1.06	1.06	1.62	2.30	1.78	1.62	2.30	1.78	ns	
HSTL_III_18	0.91	1.06	1.06	1.54	2.49	1.69	1.54	2.49	1.69	ns	
SSTL2_I	0.91	1.06	1.06	1.60	2.50	1.74	1.60	2.50	1.74	ns	
SSTL2_II	0.91	1.06	1.06	1.54	2.49	1.71	1.54	2.49	1.71	ns	
SSTL15	0.91	1.06	1.06	1.54	2.07	1.69	1.54	2.07	1.69	ns	
LVCMOS25, Slow, 2 mA	0.57	0.66	0.70	5.46	6.01	5.63	5.46	6.01	5.63	ns	
LVCMOS25, Slow, 4 mA	0.57	0.66	0.70	3.49	3.79	3.65	3.49	3.79	3.65	ns	
LVCMOS25, Slow, 6 mA	0.57	0.66	0.70	2.81	3.08	2.95	2.81	3.08	2.95	ns	
LVCMOS25, Slow, 8 mA	0.57	0.66	0.70	2.41	2.72	2.59	2.41	2.72	2.59	ns	
LVCMOS25, Slow, 12 mA	0.57	0.66	0.70	1.95	2.23	2.10	1.95	2.23	2.10	ns	
LVCMOS25, Slow, 16 mA	0.57	0.66	0.70	2.05	2.29	2.21	2.05	2.29	2.21	ns	
LVCMOS25, Slow, 24 mA	0.57	0.66	0.70	1.82	2.24	1.98	1.82	2.24	1.98	ns	
LVCMOS25, Fast, 2 mA	0.57	0.66	0.70	5.49	6.04	5.62	5.49	6.04	5.62	ns	
LVCMOS25, Fast, 4 mA	0.57	0.66	0.70	3.50	3.82	3.65	3.50	3.82	3.65	ns	
LVCMOS25, Fast, 6 mA	0.57	0.66	0.70	2.73	2.99	2.88	2.73	2.99	2.88	ns	
LVCMOS25, Fast, 8 mA	0.57	0.66	0.70	2.33	2.65	2.53	2.33	2.65	2.53	ns	
LVCMOS25, Fast, 12 mA	0.57	0.66	0.70	1.88	2.08	2.03	1.88	2.08	2.03	ns	

Table 45: IOB Switching Characteristics for the Defense-grade (XQ) Virtex-6 Devices (Cont'd)

I/O Standard	T _{IOPI}			T _{IOOP}			T _{IOTP}			Units	
	Speed Grade			Speed Grade			Speed Grade				
	-2	-1	-1L	-2	-1	-1L	-2	-1	-1L		
LVCMOS25, Fast, 16 mA	0.57	0.66	0.70	1.92	2.15	2.08	1.92	2.15	2.08	ns	
LVCMOS25, Fast, 24 mA	0.57	0.66	0.70	1.79	2.15	1.96	1.79	2.15	1.96	ns	
LVCMOS18, Slow, 2 mA	0.61	0.71	0.73	4.47	4.87	4.30	4.47	4.87	4.30	ns	
LVCMOS18, Slow, 4 mA	0.61	0.71	0.73	2.96	3.21	2.94	2.96	3.21	2.94	ns	
LVCMOS18, Slow, 6 mA	0.61	0.71	0.73	2.43	2.64	2.47	2.43	2.64	2.47	ns	
LVCMOS18, Slow, 8 mA	0.61	0.71	0.73	2.11	2.41	2.24	2.11	2.41	2.24	ns	
LVCMOS18, Slow, 12 mA	0.61	0.71	0.73	1.99	2.30	2.10	1.99	2.30	2.10	ns	
LVCMOS18, Slow, 16 mA	0.61	0.71	0.73	1.95	2.30	2.04	1.95	2.30	2.04	ns	
LVCMOS18, Fast, 2 mA	0.61	0.71	0.73	4.23	4.57	4.08	4.23	4.57	4.08	ns	
LVCMOS18, Fast, 4 mA	0.61	0.71	0.73	2.76	2.97	2.74	2.76	2.97	2.74	ns	
LVCMOS18, Fast, 6 mA	0.61	0.71	0.73	2.28	2.46	2.32	2.28	2.46	2.32	ns	
LVCMOS18, Fast, 8 mA	0.61	0.71	0.73	1.99	2.34	2.14	1.99	2.34	2.14	ns	
LVCMOS18, Fast, 12 mA	0.61	0.71	0.73	1.80	2.19	1.88	1.80	2.19	1.88	ns	
LVCMOS18, Fast, 16 mA	0.61	0.71	0.73	1.74	2.18	1.88	1.74	2.18	1.88	ns	
LVCMOS15, Slow, 2 mA	0.73	0.85	0.85	3.77	4.29	3.91	3.77	4.29	3.91	ns	
LVCMOS15, Slow, 4 mA	0.73	0.85	0.85	2.79	3.10	2.93	2.79	3.10	2.93	ns	
LVCMOS15, Slow, 6 mA	0.73	0.85	0.85	2.32	2.68	2.50	2.32	2.68	2.50	ns	
LVCMOS15, Slow, 8 mA	0.73	0.85	0.85	1.98	2.29	2.24	1.98	2.29	2.24	ns	
LVCMOS15, Slow, 12 mA	0.73	0.85	0.85	1.91	2.23	2.07	1.91	2.23	2.07	ns	
LVCMOS15, Slow, 16 mA	0.73	0.85	0.85	1.83	2.23	1.98	1.83	2.23	1.98	ns	
LVCMOS15, Fast, 2 mA	0.73	0.85	0.85	3.77	4.28	3.91	3.77	4.28	3.91	ns	
LVCMOS15, Fast, 4 mA	0.73	0.85	0.85	2.53	2.78	2.66	2.53	2.78	2.66	ns	
LVCMOS15, Fast, 6 mA	0.73	0.85	0.85	2.05	2.42	2.16	2.05	2.42	2.16	ns	
LVCMOS15, Fast, 8 mA	0.73	0.85	0.85	1.90	2.20	2.04	1.90	2.20	2.04	ns	
LVCMOS15, Fast, 12 mA	0.73	0.85	0.85	1.77	2.11	1.90	1.77	2.11	1.90	ns	
LVCMOS15, Fast, 16 mA	0.73	0.85	0.85	1.76	2.11	1.92	1.76	2.11	1.92	ns	
LVCMOS12, Slow, 2 mA	0.81	0.93	0.95	3.39	3.75	3.54	3.39	3.75	3.54	ns	
LVCMOS12, Slow, 4 mA	0.81	0.93	0.95	2.63	2.93	2.79	2.63	2.93	2.79	ns	
LVCMOS12, Slow, 6 mA	0.81	0.93	0.95	2.11	2.67	2.26	2.11	2.67	2.26	ns	
LVCMOS12, Slow, 8 mA	0.81	0.93	0.95	2.02	2.25	2.17	2.02	2.25	2.17	ns	
LVCMOS12, Fast, 2 mA	0.81	0.93	0.95	2.98	3.39	3.11	2.98	3.39	3.11	ns	
LVCMOS12, Fast, 4 mA	0.81	0.93	0.95	2.16	2.70	2.31	2.16	2.70	2.31	ns	
LVCMOS12, Fast, 6 mA	0.81	0.93	0.95	1.89	2.34	2.05	1.89	2.34	2.05	ns	
LVCMOS12, Fast, 8 mA	0.81	0.93	0.95	1.82	2.10	1.98	1.82	2.10	1.98	ns	
LVDCI_25	0.57	0.70	0.70	2.14	2.82	2.26	2.14	2.82	2.26	ns	
LVDCI_18	0.61	0.71	0.73	2.23	2.78	2.38	2.23	2.78	2.38	ns	
LVDCI_15	0.73	0.85	0.85	2.01	2.75	2.18	2.01	2.75	2.18	ns	
LVDCI_DV2_25	0.57	0.70	0.70	1.83	2.37	2.00	1.83	2.37	2.00	ns	

I/O Standard Adjustment Measurement Methodology

Input Delay Measurements

[Table 47](#) shows the test setup parameters used for measuring input delay.

Table 47: Input Delay Measurement Methodology

Description	I/O Standard Attribute	$V_L^{(1)(2)}$	$V_H^{(1)(2)}$	$V_{MEAS}^{(1)(4)(5)}$	$V_{REF}^{(1)(3)(5)}$
LVCMOS, 2.5V	LVCMOS25	0	2.5	1.25	—
LVCMOS, 1.8V	LVCMOS18	0	1.8	0.9	—
LVCMOS, 1.5V	LVCMOS15	0	1.5	0.75	—
HSTL (High-Speed Transceiver Logic), Class I & II	HSTL_I, HSTL_II	$V_{REF} - 0.5$	$V_{REF} + 0.5$	V_{REF}	0.75
HSTL, Class III	HSTL_III	$V_{REF} - 0.5$	$V_{REF} + 0.5$	V_{REF}	0.90
HSTL, Class I & II, 1.8V	HSTL_I_18, HSTL_II_18	$V_{REF} - 0.5$	$V_{REF} + 0.5$	V_{REF}	0.90
HSTL, Class III 1.8V	HSTL_III_18	$V_{REF} - 0.5$	$V_{REF} + 0.5$	V_{REF}	1.08
SSTL (Stub Terminated Transceiver Logic), Class I & II, 3.3V	SSTL3_I, SSTL3_II	$V_{REF} - 1.00$	$V_{REF} + 1.00$	V_{REF}	1.5
SSTL, Class I & II, 2.5V	SSTL2_I, SSTL2_II	$V_{REF} - 0.75$	$V_{REF} + 0.75$	V_{REF}	1.25
SSTL, Class I & II, 1.8V	SSTL18_I, SSTL18_II	$V_{REF} - 0.5$	$V_{REF} + 0.5$	V_{REF}	0.90
LVDS (Low-Voltage Differential Signaling), 2.5V	LVDS_25	1.2 – 0.125	1.2 + 0.125	0 ⁽⁶⁾	—
LVDSEXT (LVDS Extended Mode), 2.5V	LVDSEXT_25	1.2 – 0.125	1.2 + 0.125	0 ⁽⁶⁾	—
HT (HyperTransport), 2.5V	LDT_25	0.6 – 0.125	0.6 + 0.125	0 ⁽⁶⁾	—

Notes:

1. The input delay measurement methodology parameters for LVDCI are the same for LVCMOS standards of the same voltage. Input delay measurement methodology parameters for HSLVDCI are the same as for HSTL_II standards of the same voltage. Parameters for all other DCI standards are the same for the corresponding non-DCI standards.
2. Input waveform switches between V_L and V_H .
3. Measurements are made at typical, minimum, and maximum V_{REF} values. Reported delays reflect worst case of these measurements. V_{REF} values listed are typical.
4. Input voltage level from which measurement starts.
5. This is an input voltage reference that bears no relation to the V_{REF} / V_{MEAS} parameters found in IBIS models and/or noted in [Figure 6](#).
6. The value given is the differential input voltage.

Output Serializer/Deserializer Switching Characteristics

Table 52: OSERDES Switching Characteristics

Symbol	Description	Speed Grade					Units
		-3	-2	-1 (XC)	-1 (XQ)	-1L	
Setup/Hold							
T _{OSDCK_D} /T _{OSCKD_D}	D input Setup/Hold with respect to CLKDIV	0.23/ -0.10	0.28/ -0.10	0.31/ -0.10	0.35/ -0.10	0.36/ -0.15	ns
T _{OSDCK_T} /T _{OSCKD_T} ⁽¹⁾	T input Setup/Hold with respect to CLK	0.44/ -0.10	0.51/ -0.09	0.56/ -0.08	0.60/ -0.08	0.68/ -0.15	ns
T _{OSDCK_T2} /T _{OSCKD_T2} ⁽¹⁾	T input Setup/Hold with respect to CLKDIV	0.25/ -0.10	0.27/ -0.09	0.31/ -0.08	0.31/ -0.08	0.47/ -0.15	ns
T _{OSCCK_OCE} /T _{OSCKC_OCE}	OCE input Setup/Hold with respect to CLK	0.17/ -0.03	0.20/ -0.03	0.22/ -0.03	0.27/ -0.03	0.27/ -0.04	ns
T _{OSCCK_S}	SR (Reset) input Setup with respect to CLKDIV	0.07	0.07	0.07	0.07	0.08	ns
T _{OSCCK_TCE} /T _{OSCKC_TCE}	TCE input Setup/Hold with respect to CLK	0.15/ -0.04	0.19/ -0.04	0.21/ -0.04	0.27/ -0.04	0.29/ -0.05	ns
Sequential Delays							
T _{OSCKO_OQ}	Clock to out from CLK to OQ	0.63	0.71	0.82	0.82	0.93	ns
T _{OSCKO_TQ}	Clock to out from CLK to TQ	0.63	0.71	0.82	0.82	0.93	ns
Combinatorial							
T _{OSDO_TTQ}	T input to TQ Out	0.76	0.84	0.97	0.97	1.11	ns

Notes:

1. T_{OSDCK_T2} and T_{OSCKD_T2} are reported as T_{OSDCK_T}/T_{OSCKD_T} in TRACE report.

Input/Output Delay Switching Characteristics

Table 53: Input/Output Delay Switching Characteristics

Symbol	Description	Speed Grade				Units
		-3	-2	-1	-1L	
IDELAYCTRL						
T _{DLYCCO_RDY}	Reset to Ready for IDELAYCTRL	3.00	3.00	3.00	3.25	μs
F _{IDELAYCTRL_REF}	REFCLK frequency = 200.0 ⁽¹⁾	200	200	200	200	MHz
	REFCLK frequency = 300.0 ⁽¹⁾	300	300	—	—	MHz
IDELAYCTRL_REF_PRECISION	REFCLK precision	±10	±10	±10	±10	MHz
T _{IDELAYCTRL_RPW}	Minimum Reset pulse width	50.00	50.00	50.00	52.50	ns
IODELAY						
T _{IDELAYRESOLUTION}	IODELAY Chain Delay Resolution	1/(32 x 2 x F _{REF})				ps
T _{IDELAYPAT_JIT}	Pattern dependent period jitter in delay chain for clock pattern. ⁽²⁾	0	0	0	0	ps per tap
	Pattern dependent period jitter in delay chain for random data pattern (PRBS 23). ⁽³⁾	±5	±5	±5	±5	ps per tap
	Pattern dependent period jitter in delay chain for random data pattern (PRBS 23). ⁽⁴⁾	±9	±9	±9	±9	ps per tap
T _{IODELAY_CLK_MAX}	Maximum frequency of CLK input to IODELAY	500.00	420.00	300.00	300.00	MHz
T _{IODCCK_CE} / T _{IODCKC_CE}	CE pin Setup/Hold with respect to CK	0.45/ -0.09	0.53/ -0.09	0.65/ -0.09	0.84/ -0.14	ns
T _{IODCK_INC} / T _{IODCKC_INC}	INC pin Setup/Hold with respect to CK	0.23/ -0.02	0.27/ -0.01	0.31/ 0.00	0.27/ -0.04	ns
T _{IODCCK_RST} / T _{IODCKC_RST}	RST pin Setup/Hold with respect to CK	0.57/ -0.08	0.62/ -0.08	0.69/ -0.08	0.74/ -0.13	ns
T _{IODDO_T}	TSCONTROL delay to MUXE/MUXF switching and through IODELAY	Note 5	Note 5	Note 5	Note 5	ps
T _{IODDO_IDATAIN}	Propagation delay through IODELAY	Note 5	Note 5	Note 5	Note 5	ps
T _{IODDO_ODATAIN}	Propagation delay through IODELAY	Note 5	Note 5	Note 5	Note 5	ps

Notes:

1. Average Tap Delay at 200 MHz = 78 ps, at 300 MHz = 52 ps.
2. When HIGH_PERFORMANCE mode is set to TRUE or FALSE.
3. When HIGH_PERFORMANCE mode is set to TRUE
4. When HIGH_PERFORMANCE mode is set to FALSE.
5. Delay depends on IODELAY tap setting. See TRACE report for actual values.

CLB Switching Characteristics

Table 54: CLB Switching Characteristics

Symbol	Description	Speed Grade				Units
		-3	-2	-1	-1L	
Combinatorial Delays						
T _{ILO}	An – Dn LUT address to A	0.06	0.07	0.07	0.09	ns, Max
	An – Dn LUT address to AMUX/CMUX	0.18	0.20	0.22	0.25	ns, Max
	An – Dn LUT address to BMUX_A	0.28	0.31	0.36	0.40	ns, Max

Table 59: Configuration Switching Characteristics (Cont'd)

Symbol	Description	Speed Grade				Units
		-3	-2	-1	-1L	
T _{MMCMDCK_DI} / T _{MMCMCKD_DI}	DI Setup/Hold	1.25/ 0.00	1.40/ 0.00	1.63/ 0.00	1.64/ 0.00	ns
T _{MMCMDCK_DEN} / T _{MMCMCKD_DEN}	DEN Setup/Hold time	1.25/ 0.00	1.40/ 0.00	1.63/ 0.00	1.64/ 0.00	ns
T _{MMCMDCK_DWE} / T _{MMCMCKD_DWE}	DWE Setup/Hold time	1.25/ 0.00	1.40/ 0.00	1.63/ 0.00	1.64/ 0.00	ns
T _{MMCMCKO_DO}	CLK to out of DO ⁽³⁾	2.60	3.02	3.64	3.68	ns
T _{MMCMCKO_DRDY}	CLK to out of DRDY	0.32	0.34	0.38	0.38	ns

Notes:

1. To support longer delays in configuration, use the design solutions described in [UG360: Virtex-6 FPGA Configuration User Guide](#).
2. Only during configuration, the last edge is determined by a weak pull-up/pull-down resistor in the I/O.
3. DO will hold until next DRP operation.

Clock Buffers and Networks

Table 60: Global Clock Switching Characteristics (Including BUFGCTRL)

Symbol	Description	Devices	Speed Grade				Units
			-3	-2	-1	-1L	
T _{BCCCK_CE} / T _{BCCKC_CE} ⁽¹⁾	CE pins Setup/Hold	All	0.11/ 0.00	0.13/ 0.00	0.16/ 0.00	0.13/ 0.00	ns
T _{BCCCK_S} / T _{BCCKC_S} ⁽¹⁾	S pins Setup/Hold	All	0.11/ 0.00	0.13/ 0.00	0.16/ 0.00	0.13/ 0.00	ns
T _{BGCKO_O} ⁽²⁾	BUFGCTRL delay from I0/I1 to O	All	0.07	0.08	0.10	0.10	ns
Maximum Frequency							
F _{MAX}	Global clock tree (BUFG)	All except LX760	800	750	700	667	MHz
		LX760	N/A	700	700	667	MHz

Notes:

1. T_{BCCCK_CE} and T_{BCCKC_CE} must be satisfied to assure glitch-free operation of the global clock when switching between clocks. These parameters do not apply to the BUFGMUX_VIRTEX4 primitive that assures glitch-free operation. The other global clock setup and hold times are optional; only needing to be satisfied if device operation requires simulation matches on a cycle-for-cycle basis when switching between clocks.
2. T_{BGCKO_O} (BUFG delay from I0 to O) values are the same as T_{BGCKO_O} values.

Table 61: Input/Output Clock Switching Characteristics (BUFIO)

Symbol	Description	Speed Grade				Units
		-3	-2	-1	-1L	
T _{BLOCKO_O}	Clock to out delay from I to O	0.14	0.16	0.18	0.21	ns
Maximum Frequency						
F _{MAX}	I/O clock tree (BUFIO)	800	800	710	710	MHz

Table 62: Regional Clock Switching Characteristics (BUFR)

Symbol	Description	Speed Grade				Units
		-3	-2	-1	-1L	
T _{BRCKO_O}	Clock to out delay from I to O	0.56	0.62	0.73	0.82	ns
T _{BRCKO_O_BYP}	Clock to out delay from I to O with Divide Bypass attribute set	0.28	0.31	0.36	0.41	ns

Table 62: Regional Clock Switching Characteristics (BUFR) (Cont'd)

Symbol	Description	Speed Grade				Units
		-3	-2	-1	-1L	
T _{BRDO_O}	Propagation delay from CLR to O	0.69	0.74	0.80	1.12	ns
Maximum Frequency						
F _{MAX} ⁽¹⁾	Regional clock tree (BUFR)	500	420	300	300	MHz

Notes:

1. The maximum input frequency to the BUFR is the BUFIo F_{MAX} frequency.

Table 63: Horizontal Clock Buffer Switching Characteristics (BUFH)

Symbol	Description	Speed Grade				Units
		-3	-2	-1	-1L	
T _{BHCKO_O}	BUFH delay from I to O	0.10	0.11	0.13	0.15	ns
T _{BHCKC_CE} /T _{BHCKC_CE}	CE pin Setup and Hold	0.04/ 0.04	0.04/ 0.04	0.05/ 0.05	0.04/ 0.04	ns
Maximum Frequency						
F _{MAX}	Horizontal clock buffer (BUFH)	800	750	700	667	MHz

MMCM Switching Characteristics

Table 64: MMCM Specification

Symbol	Description	Speed Grade				Units
		-3	-2	-1	-1L	
F _{INMAX}	Maximum Input Clock Frequency ⁽¹⁾	800	750	700	700	MHz
F _{INMIN}	Minimum Input Clock Frequency	10	10	10	10	MHz
F _{INJITTER}	Maximum Input Clock Period Jitter	< 20% of clock input period or 1 ns Max				
F _{INDUTY} ⁽²⁾	Allowable Input Duty Cycle: 10—49 MHz	25/75				%
	Allowable Input Duty Cycle: 50—199 MHz	30/70				%
	Allowable Input Duty Cycle: 200—399 MHz	35/65				%
	Allowable Input Duty Cycle: 400—499 MHz	40/60				%
	Allowable Input Duty Cycle: >500 MHz	45/55				%
F _{MIN_PSCLK}	Minimum Dynamic Phase Shift Clock Frequency	0.01	0.01	0.01	0.01	MHz
F _{MAX_PSCLK}	Maximum Dynamic Phase Shift Clock Frequency	550	500	450	450	MHz
F _{VCOMIN}	Minimum MMCM VCO Frequency	600	600	600	600	MHz
F _{VCOMAX}	Maximum MMCM VCO Frequency	1600	1440	1200	1200	MHz
F _{BANDWIDTH}	Low MMCM Bandwidth at Typical ⁽³⁾	1.00	1.00	1.00	1.00	MHz
	High MMCM Bandwidth at Typical ⁽³⁾	4.00	4.00	4.00	4.00	MHz
T _{STATPHAOFFSET}	Static Phase Offset of the MMCM Outputs ⁽⁴⁾	0.12	0.12	0.12	0.12	ns
T _{OUTJITTER}	MMCM Output Jitter ⁽⁵⁾	Note 3				
T _{OUTDUTY}	MMCM Output Clock Duty Cycle Precision ⁽⁶⁾	0.15	0.20	0.20	0.20	ns
T _{LOCKMAX}	MMCM Maximum Lock Time	100	100	100	100	μs
F _{OUTMAX}	MMCM Maximum Output Frequency	800	750	700	700	MHz
F _{OUTMIN}	MMCM Minimum Output Frequency ⁽⁷⁾⁽⁸⁾	4.69	4.69	4.69	4.69	MHz
T _{EXTFDVAR}	External Clock Feedback Variation	< 20% of clock input period or 1 ns Max				

Table 67: Clock-Capable Clock Input to Output Delay With MMCM

Symbol	Description	Device	Speed Grade				Units
			-3	-2	-1	-1L	
LVCMOS25 Clock-capable Clock Input to Output Delay using Output Flip-Flop, 12mA, Fast Slew Rate, <i>with</i> MMCM.							
TICKOFMMCMCC	Clock-capable Clock Input and OUTFF <i>with</i> MMCM	XC6VLX75T	2.22	2.38	2.63	2.72	ns
		XC6VLX130T	2.24	2.39	2.65	2.74	ns
		XC6VLX195T	2.24	2.40	2.65	2.75	ns
		XC6VLX240T	2.24	2.40	2.65	2.75	ns
		XC6VLX365T	2.25	2.42	2.65	2.76	ns
		XC6VLX550T	N/A	2.43	2.68	2.80	ns
		XC6VLX760	N/A	2.42	2.69	2.79	ns
		XC6VSX315T	2.23	2.38	2.65	2.73	ns
		XC6VSX475T	N/A	2.30	2.57	2.66	ns
		XC6VHX250T	2.25	2.41	2.67	N/A	ns
		XC6VHX255T	2.35	2.51	2.78	N/A	ns
		XC6VHX380T	2.27	2.43	2.69	N/A	ns
		XC6VHX565T	N/A	2.41	2.68	N/A	ns
		XQ6VLX130T	N/A	2.39	2.65	2.74	ns
		XQ6VLX240T	N/A	2.40	2.65	2.75	ns
		XQ6VLX550T	N/A	N/A	2.68	2.80	ns
		XQ6VSX315T	N/A	2.38	2.65	2.73	ns
		XQ6VSX475T	N/A	N/A	2.57	2.66	ns

Notes:

1. Listed above are representative values where one global clock input drives one vertical clock line in each accessible column, and where all accessible IOB and CLB flip-flops are clocked by the global clock net.
2. MMCM output jitter is already included in the timing calculation.